Amendments to the Specification:

Please replace the paragraph beginning at page 3, line 22 with the following amended paragraph:

b) The BE-electrode 209 is then etched as steeply as possible and the cover layer 403 is deposited. Next the dielectric layer 222 is applied. To protect the capacitor and bottom electrode during the etching of the hole for a VO-contact 405 through the layer 222, the cover layer 403 serves as both an etch stop liner and as a cover. A highly selective etch is used which stops on the cover layer 403. Then, an alumina spacer 4000 is deposited on the side walls of the hole. Due to the effect of the spacer, the cover layer 403 remains intact on BE-sidewalls 407. The result is almost vertical BE sidewalls 407, good step coverage for the ALD-deposition of Alumina inside the VO-contact hole 405, highly selective etch of the hole for the VO-contact 4085, and no 'noses" (no "noses" means that the sidewalls of the VO-contact hole 405 are smooth), thus providing a good Alumina spacer 4000 deposited on the walls of the VO-contact hole 405.

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